

Transistors

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	V _{DSS}	-20	V	
Gate-source voltage	V _{GSS}	±12	V	
Drain current	Continuous	I _D	±1.5	A
	Pulsed	I _{DP} *1	±6	A
Source current (Body diode)	Continuous	I _S *1	-0.6	A
	Pulsed	I _{SP}	-6	A
Total power dissipation	P _D *2	0.8	W	
Channel temperature	T _{ch}	150	°C	
Range of Storage temperature	T _{stg}	-55 to +150	°C	

*1 Pw≤10μs, Duty cycle≤1%

*2 Mounted on a ceramic board

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μA	V _{GS} =±12V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	-20	-	-	V	I _D =-1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	-1	μA	V _{DS} =-20V, V _{GS} =0V
Gate threshold voltage	V _{GS(th)}	-0.7	-	-2.0	V	V _{DS} =-10V, I _D =-1mA
Static drain-source on-state resistance	R _{DS(on)} *	-	100	135	mΩ	I _D =-1.5A, V _{GS} =-4.5V
		-	110	150	mΩ	I _D =-1.5A, V _{GS} =-4V
		-	180	250	mΩ	I _D =-1.5A, V _{GS} =-2.5V
Forward transfer admittance	Y _{fs} *	1.5	-	-	S	V _{DS} =-10V, I _D =-0.8A
Input capacitance	C _{iss}	-	560	-	pF	V _{DS} =-10V
Output capacitance	C _{oss}	-	90	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	-	55	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	12	-	ns	I _D =-0.8A
Rise time	t _r *	-	12	-	ns	V _{DD} ≐-15V
Turn-off delay time	t _{d(off)} *	-	38	-	ns	V _{GS} =-4.5V
Fall time	t _f *	-	12	-	ns	R _L =9Ω
Total gate charge	Q _g	-	5.2	-	nC	V _{DD} ≐-15V R _L ≐10Ω
Gate-source charge	Q _{gs}	-	1.3	-	nC	V _{GS} =-4.5V R _{GS} =10Ω
Gate-drain charge	Q _{gd}	-	1.4	-	nC	I _D =-1.5A

*Pulsed

Body diode characteristics (source-drain characteristics)

Forward voltage	V _{SD}	-	-	-1.2	V	I _S =-0.6A, V _{GS} =0V
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Transistors

●Electrical characteristic curves

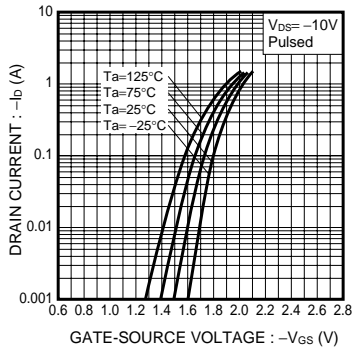


Fig.1 Typical Transfer Characteristics

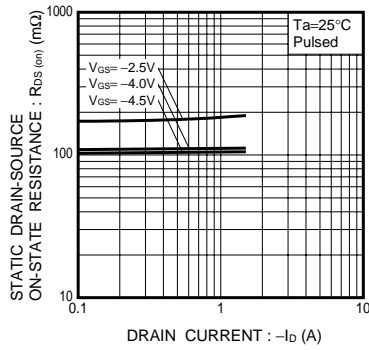


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

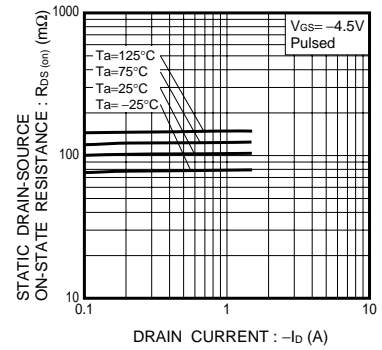


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

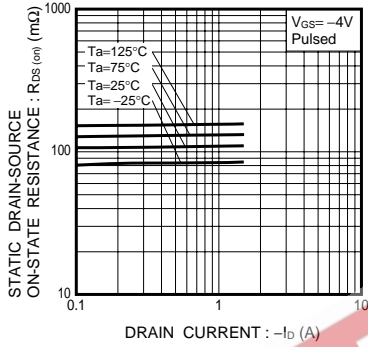


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

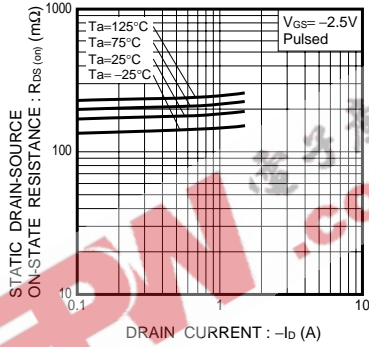


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

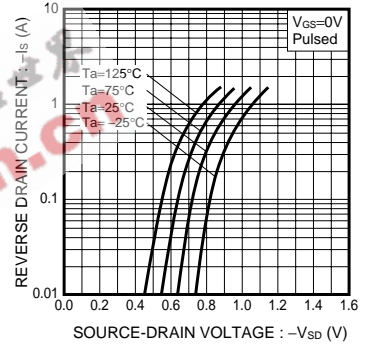


Fig.6 Reverse Drain Current vs. Source-Drain Voltage

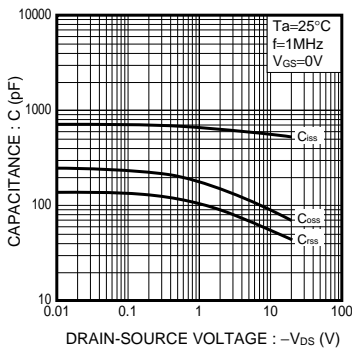


Fig.7 Typical Capacitance vs. Drain-Source Voltage

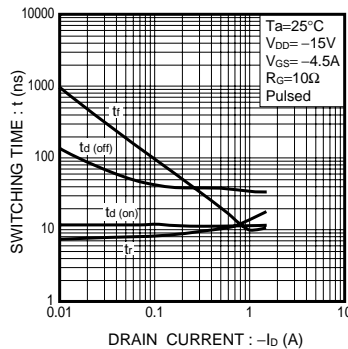


Fig.8 Switching Characteristics

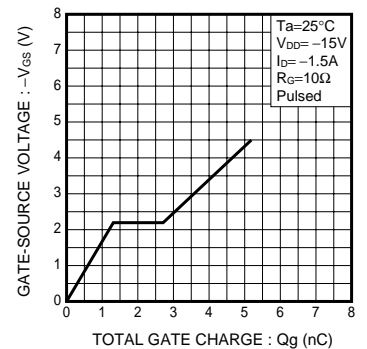


Fig.9 Dynamic Input Characteristics

Transistors

●Measurement circuits

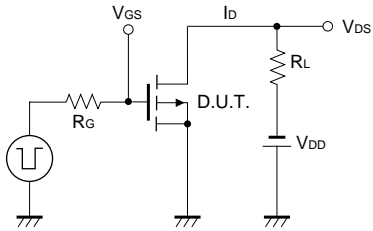


Fig.10 Switching Time Measurement Circuit

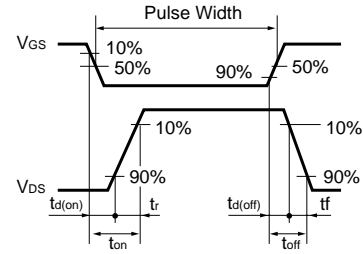


Fig.11 Switching Waveforms

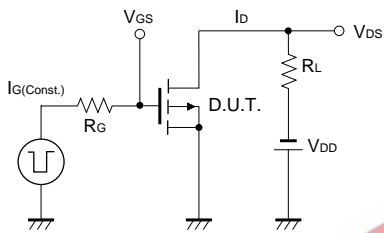


Fig.12 Gate Charge Measurement Circuit

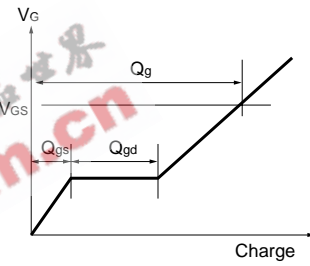


Fig.13 Gate Charge Waveforms

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